Preliminary

TOSHIBA Multi Chip Discrete Device

HN7G01FU

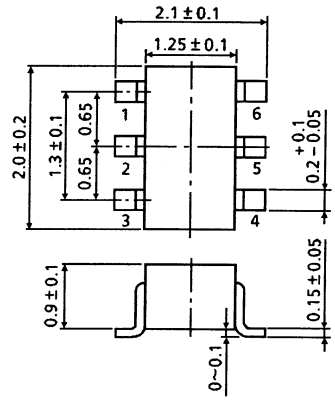
Power Management Switch Application

Driver Circuit Application

Interface Circuit Application

- Q1 (transistor): 2SA1955 equivalent
- Q2 (MOS-FET): 2SK1830 equivalent

Unit: mm



1. EMITTER
2. BASE
3. DRAIN
4. SOURCE
5. GATE
6. COLLECTOR

US6

JEDEC	—
JEITA	—
TOSHIBA	—

Weight: 6.8 mg (typ.)

Q1 (transistor) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−15	V
Collector-emitter voltage	V_{CEO}	−12	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−400	mA
Base current	I_B	−50	mA

Q2 (MOS-FET) Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GSS}	10	V
Drain current	I_D	50	mA

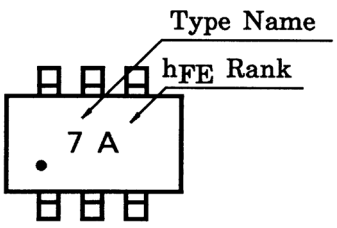
Q1, Q2 Common Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power dissipation	P_C (Note 1)	200	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~150	°C

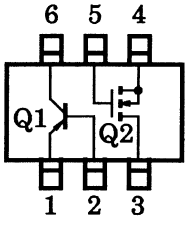
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

Marking



Pin Assignment (top view)



Q1 (transistor) Electrical Characteristics (Ta = 25°C)

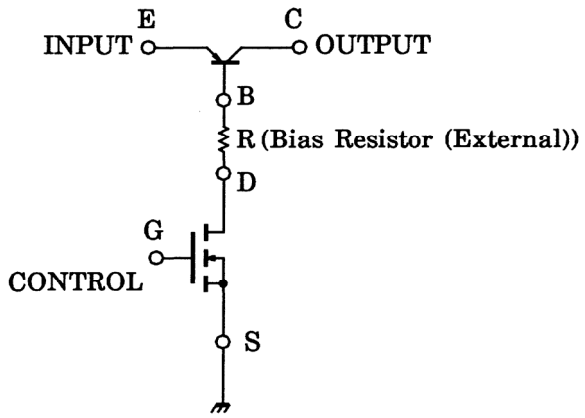
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −15 V, I_E = 0	—	—	−0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−0.1	mA
DC current gain	h_{FE} (Note 2)	V_{CE} = −2 V, I_C = −10 mA	300	—	1000	
Collector-emitter saturation voltage	$V_{CE\ (sat)\ (1)}$	I_C = −10 mA, I_B = −0.5 mA	—	−15	−30	mV
	$V_{CE\ (sat)\ (2)}$	I_C = −200 mA, I_B = −10 mA	—	−110	−250	
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C = −200 mA, I_B = −10 mA	—	−0.87	−1.2	V

Note 2: h_{FE} classification A: 300~600, B: 500~1000

Q2 (MOS-FET) Electrical Characteristics (Ta = 25°C)

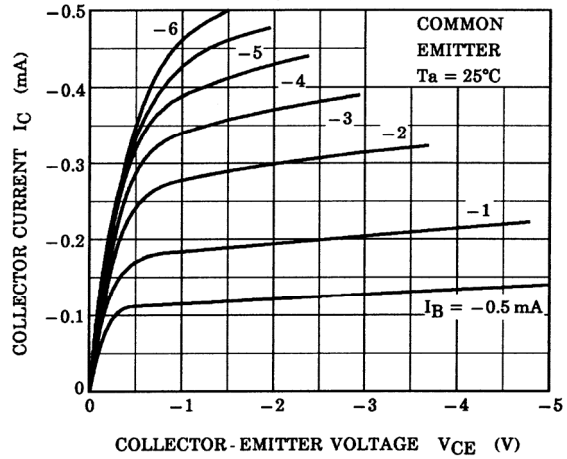
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = 10 V, V_{DS} = 0	—	—	1	μA
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	I_D = 100 μA, V_{GS} = 0	20	—	—	V
Drain current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate threshold voltage	V_{th}	V_{DS} = 3 V, I_D = 0.1 mA	0.5	—	1.5	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 10 mA	20	—	—	mS
Drain-source ON resistance	$R_{DS\ (ON)}$	I_D = 10 mA, V_{GS} = 2.5 V	—	20	40	Ω

Application Example (power management switch)

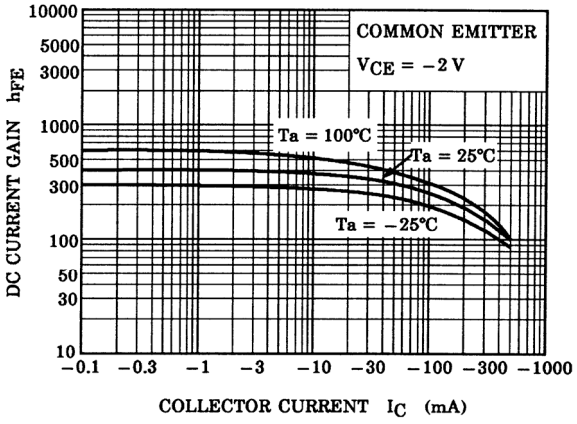


Transistor

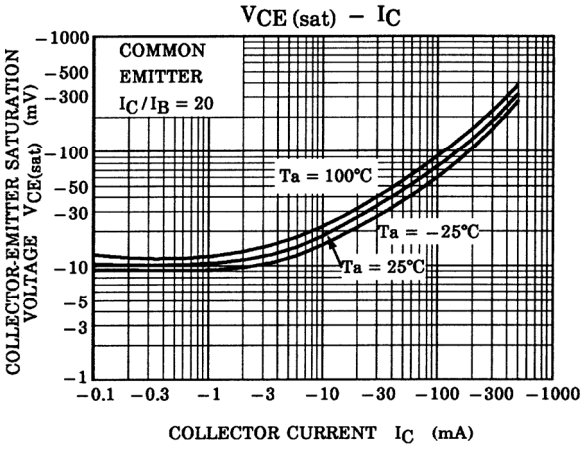
$I_C - V_{CE}$



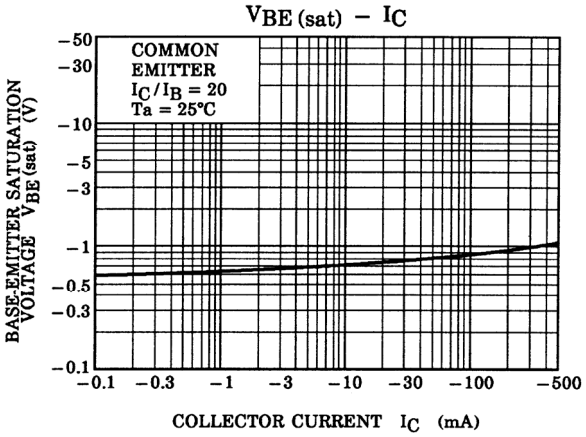
$h_{FE} - I_C$



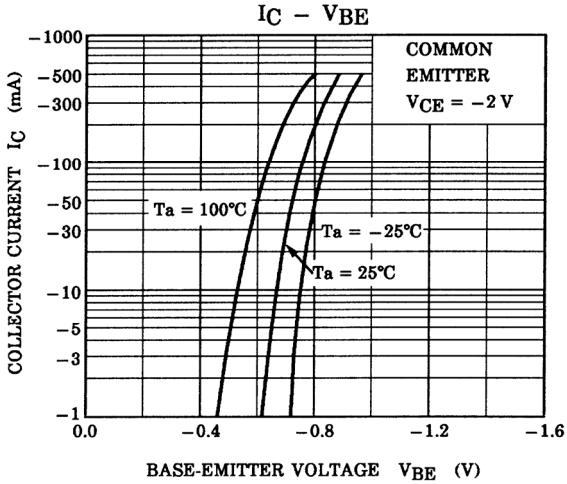
$V_{CE\,(sat)} - I_C$



$V_{BE\,(sat)} - I_C$

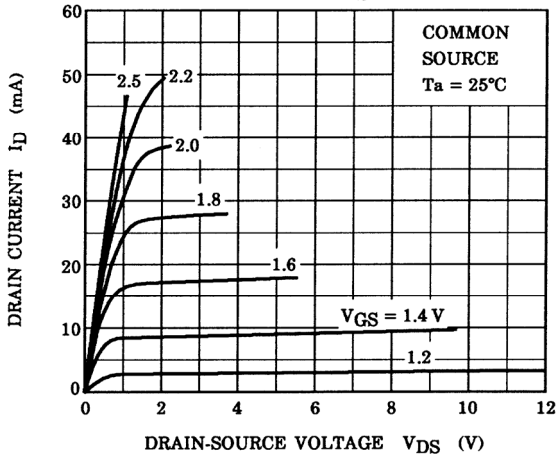


$I_C - V_{BE}$

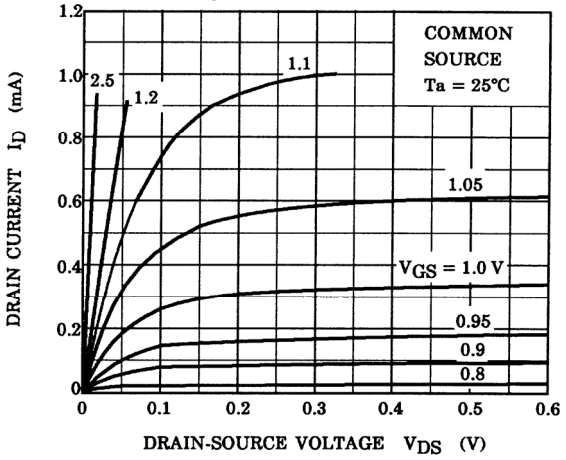


MOS-FET

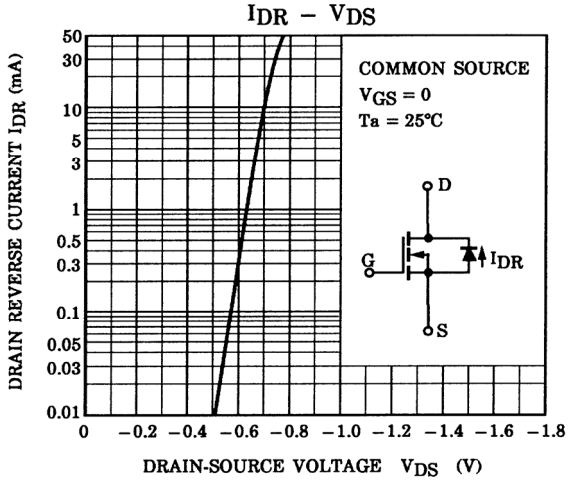
I_D – V_{DS}



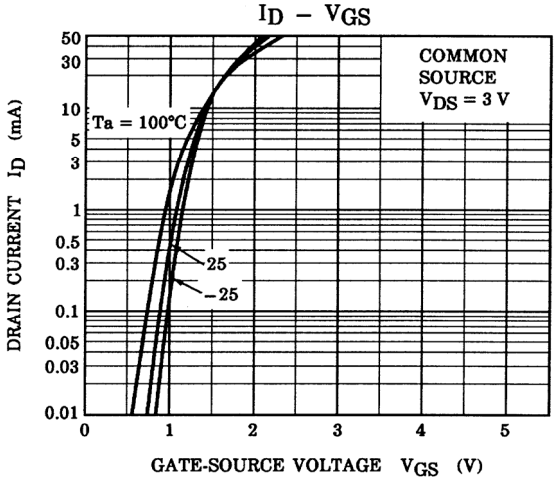
I_D – V_{DS} (LOW VOLTAGE REGION)



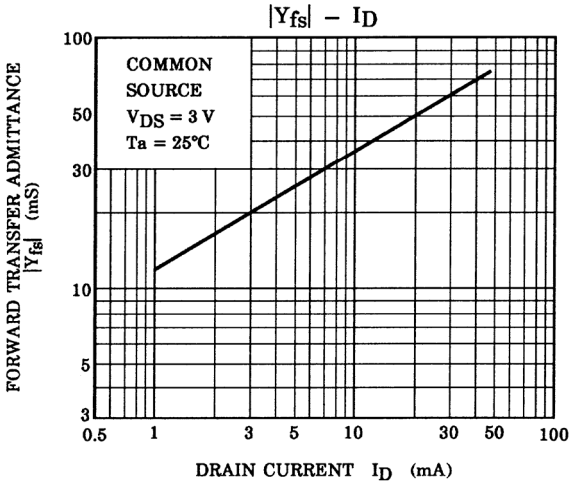
I_{DR} – V_{DS}



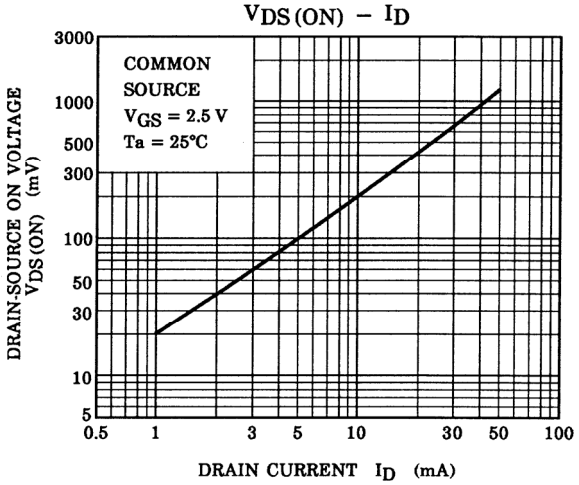
I_D – V_{GS}



$|Y_{fs}|$ – I_D



$V_{DS(ON)}$ – I_D



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20070701-EN GENERAL

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